

### HALF-BRIDGE DRIVER

#### **Features**

- Floating channel designed for bootstrap operation Fully operational to +600V
   Tolerant to negative transient voltage dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout
- 3.3V, 5V and 15V input logic compatible
- Cross-conduction prevention logic
- Internally set deadtime
- High side output in phase with input
- Shut down input turns off both channels
- Matched propagation delay for both channels
- Also available LEAD-FREE

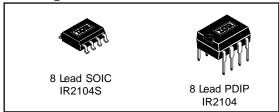
### **Description**

The IR2104(S) are high voltage, high speed power MOSFET and IGBT drivers with dependent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized

### **Product Summary**

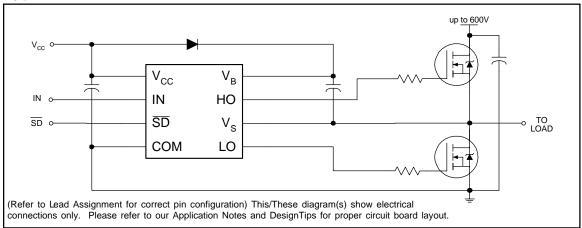
Voffset	600V max.
I <sub>O</sub> +/-	130 mA / 270 mA
Vout	10 - 20V
t <sub>on/off</sub> (typ.)	680 & 150 ns
Deadtime (typ.)	520 ns

### **Packages**



monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates from 10 to 600 volts.

### **Typical Connection**



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### **Absolute Maximum Ratings**

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition		Min.	Max.	Units
V <sub>B</sub>	High side floating absolute voltage		-0.3	625	
Vs	High side floating supply offset voltage		V <sub>B</sub> - 25	V <sub>B</sub> + 0.3	
V <sub>HO</sub>	High side floating output voltage		V <sub>S</sub> - 0.3	V <sub>B</sub> + 0.3	
Vcc	Low side and logic fixed supply voltage	-0.3	25	V	
V <sub>LO</sub>	Low side output voltage		-0.3	V <sub>CC</sub> + 0.3	
V <sub>IN</sub>	Logic input voltage (IN & SD)		-0.3	V <sub>CC</sub> + 0.3	
dV <sub>s</sub> /dt	Allowable offset supply voltage transient		_	50	V/ns
PD	Package power dissipation @ T <sub>A</sub> ≤ +25°C	(8 lead PDIP)	_	1.0	14/
		(8 lead SOIC)	_	0.625	W
RthJA	Thermal resistance, junction to ambient	(8 lead PDIP)	_	125	°C/W
		(8 lead SOIC)	_	200	C/VV
TJ	Junction temperature		_	150	
T <sub>S</sub>	Storage temperature		-55	150	°C
TL	Lead temperature (soldering, 10 seconds)		_	300	

### **Recommended Operating Conditions**

The Input/Output logic timing diagram is shown in Figure 1. For proper operation the device should be used within the recommended conditions. The  $V_S$  offset rating is tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
V <sub>B</sub>	High side floating supply absolute voltage	V <sub>S</sub> + 10	V <sub>S</sub> + 20	
Vs	High side floating supply offset voltage	Note 1	600	
V <sub>HO</sub>	High side floating output voltage	Vs	V <sub>B</sub>	v
V <sub>CC</sub>	Low side and logic fixed supply voltage	10	20	v
V <sub>LO</sub>	Low side output voltage	0	Vcc	
V <sub>IN</sub>	Logic input voltage (IN & SD)	0	Vcc	
T <sub>A</sub>	Ambient temperature	-40	125	°C

Note 1: Logic operational for  $V_S$  of -5 to +600V. Logic state held for  $V_S$  of -5V to -V<sub>BS</sub>. (Please refer to the Design Tip DT97-3 for more details).

 $\label{eq:Dynamic Electrical Characteristics} $$V_{BIAS} (V_{CC}, V_{BS}) = 15V, C_L = 1000 \ pF \ and \ T_A = 25^{\circ}C \ unless \ otherwise \ specified.$ 

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
ton	Turn-on propagation delay	_	680	820		V <sub>S</sub> = 0V
toff	Turn-off propagation delay	_	150	220		V <sub>S</sub> = 600V
t <sub>sd</sub>	Shutdown propagation delay	_	160	220		
tr	Turn-on rise time	_	100	170	ns	
tf	Turn-off fall time	_	50	90		
DT	Deadtime, LS turn-off to HS turn-on &	400	520	650		
	HS turn-on to LS turn-off					
MT	Delay matching, HS & LS turn-on/off			60		

#### **Static Electrical Characteristics**

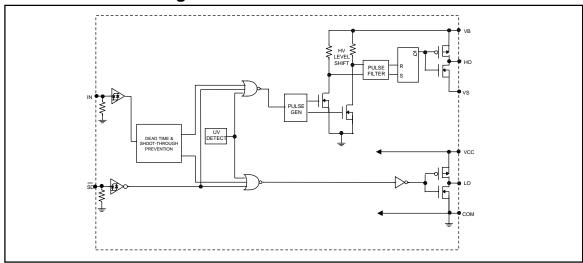
 $V_{BIAS}$  ( $V_{CC}$ ,  $V_{BS}$ ) = 15V and  $T_A$  = 25°C unless otherwise specified. The  $V_{IN}$ ,  $V_{TH}$  and  $I_{IN}$  parameters are referenced to COM. The  $V_O$  and  $I_O$  parameters are referenced to COM and are applicable to the respective output leads: HO or LO.

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
VIH	Logic "1" (HO) & Logic "0" (LO) input voltage	3	_	_		V <sub>CC</sub> = 10V to 20V
V <sub>IL</sub>	Logic "0" (HO) & Logic "1" (LO) input voltage	_	_	0.8	.,	V <sub>CC</sub> = 10V to 20V
V <sub>SD,TH+</sub>	SD input positive going threshold	3	_	_	V	V <sub>CC</sub> = 10V to 20V
V <sub>SD,TH</sub> -	SD input negative going threshold	_	_	0.8		V <sub>CC</sub> = 10V to 20V
VoH	High level output voltage, V <sub>BIAS</sub> - V <sub>O</sub>	_	_	100	\/	I <sub>O</sub> = 0A
VoL	Low level output voltage, VO	_	_	100	mV	I <sub>O</sub> = 0A
I <sub>LK</sub>	Offset supply leakage current	_	_	50		$V_{B} = V_{S} = 600V$
IQBS	Quiescent V <sub>BS</sub> supply current	_	30	55		V <sub>IN</sub> = 0V or 5V
IQCC	Quiescent V <sub>CC</sub> supply current	_	150	270	μΑ	V <sub>IN</sub> = 0V or 5V
I <sub>IN+</sub>	Logic "1" input bias current	_	3	10		V <sub>IN</sub> = 5V
I <sub>IN-</sub>	Logic "0" input bias current	_	_	1		V <sub>IN</sub> = 0V
Vccuv+	V <sub>CC</sub> supply undervoltage positive going	8	8.9	9.8		
	threshold				V	
V <sub>CCUV</sub> -	V <sub>CC</sub> supply undervoltage negative going threshold	7.4	8.2	9	·	
I <sub>O+</sub>	Output high short circuit pulsed current	130	210	_		V <sub>O</sub> = 0V
					mA	PW ≤ 10 µs
I <sub>O</sub> -	Output low short circuit pulsed current	270	360	_	шА	V <sub>O</sub> = 15V
						PW ≤ 10 µs

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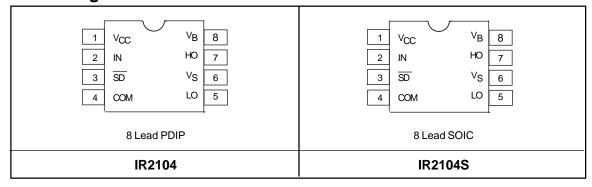
### **Functional Block Diagram**



### **Lead Definitions**

Symbol	Description
IN	Logic input for high and low side gate driver outputs (HO and LO), in phase with HO
SD	Logic input for shutdown
VB	High side floating supply
НО	High side gate drive output
Vs	High side floating supply return
Vcc	Low side and logic fixed supply
LO	Low side gate drive output
COM	Low side return

### **Lead Assignments**



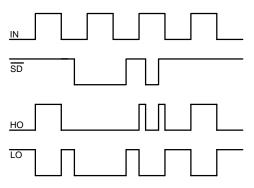


Figure 1. Input/Output Timing Diagram

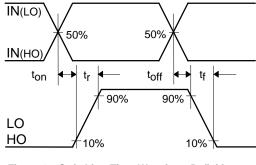


Figure 2. Switching Time Waveform Definitions

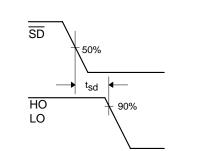


Figure 3. Shutdown Waveform Definitions

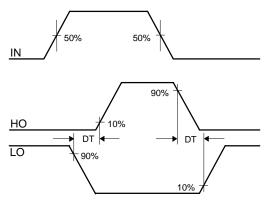


Figure 4. Deadtime Waveform Definitions

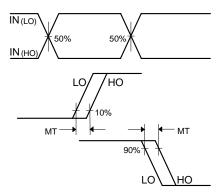


Figure 5. Delay Matching Waveform Definitions

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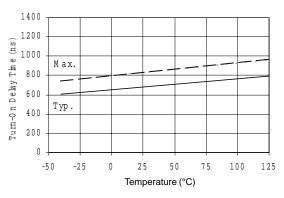


Figure 6A. Turn-On Time vs Temperature

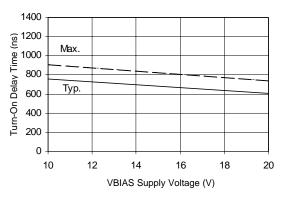


Figure 6B. Turn-On Time vs Supply Voltage

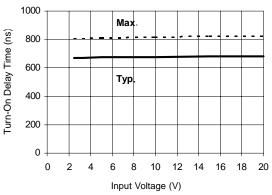


Figure 6C. Turn-On Time vs Input Voltage

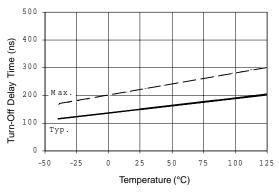


Figure 7A. Turn-Off Time vs Temperature

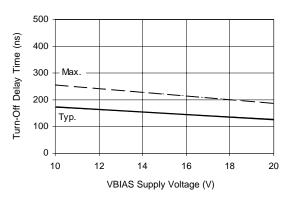


Figure 7B. Turn-Off Time vs Supply Voltage

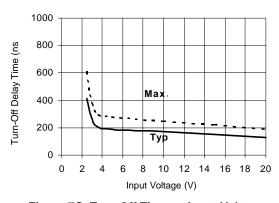


Figure 7C. Turn-Off Time vs Input Voltage

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## IR2104(S)&(PbF)

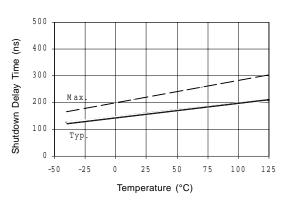


Figure 8A. Shutdown Time vs Temperature

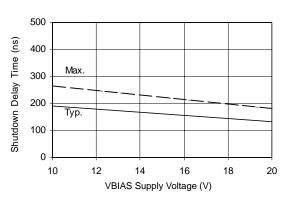


Figure 8B. Shutdown Time vs Voltage

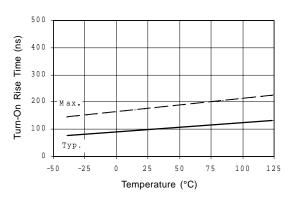


Figure 9A. Turn-On Rise Time vs Temperature

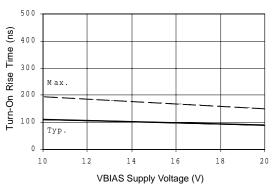


Figure 9B. Turn-On Rise Time vs Voltage

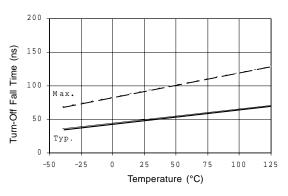


Figure 10A. Turn-Off Fall Time vs Temperature

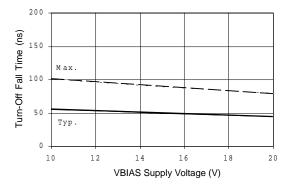


Figure 10B. Turn-Off Fall Time vs Voltage

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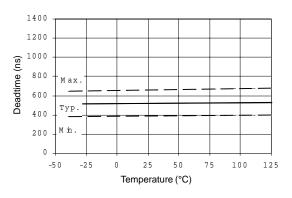


Figure 11A. Deadtime vs Temperature

7 6

5

4

3

2

0

hputVolage (V)

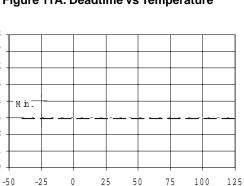


Figure 12A. Logic "1" (HO) & Logic "0" (LO) & Inactive SD Input Voltage vs Temperature

Temperature (°C)

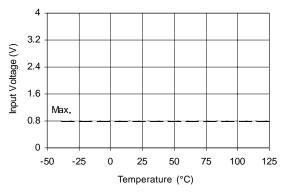


Figure 13A. Logic "0" (HO) & Logic "1" (LO) & Active SD Input Voltage vs Temperature

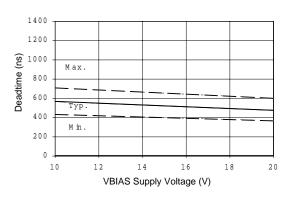


Figure 11B. Deadtime vs Voltage

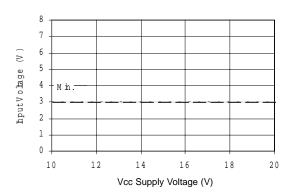


Figure 12B. Logic "1" (HO) & Logic "0" (LO) & Inactive SD Input Voltage vs Voltage

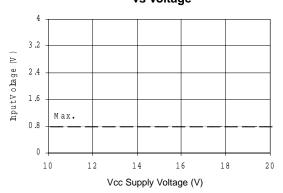
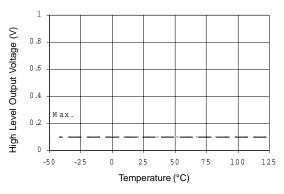


Figure 13B. Logic "0" (HO) & Logic "1" (LO) & Active SD Input Voltage vs Voltage

## International TOR Rectifier

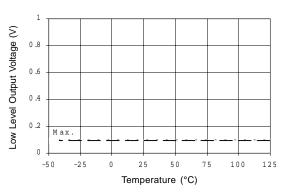
## IR2104(S)&(PbF)



(2) 0.8 0.8 0.6 0.4 0.2 Max. 0.2 14 16 18 20 Vcc Supply Voltage (V)

Figure 14A. High Level Output vs Temperature

Figure 14B. High Level Output vs Voltage



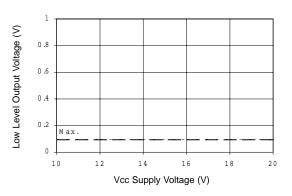
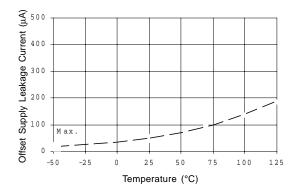


Figure 15A. Low Level Output vs Temperature

Figure 15B. Low level Output vs Voltage



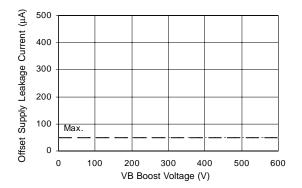


Figure 16A. Offset Supply Current vs Temperature

Figure 16B. Offset Supply Current vs Voltage

# International IOR Rectifier

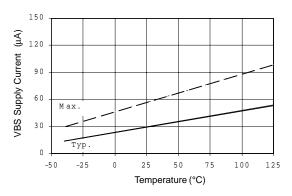


Figure 17A. VBS Supply Current vs Temperature

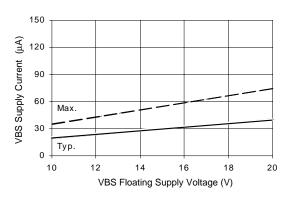


Figure 17B. V<sub>BS</sub> Supply Current vs Voltage

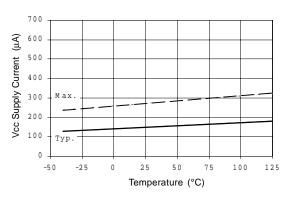


Figure 18A. Vcc Supply Current vs Temperature

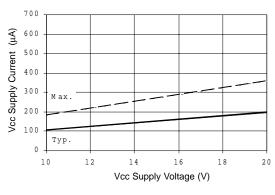


Figure 18B. Vcc Supply Current vs Voltage

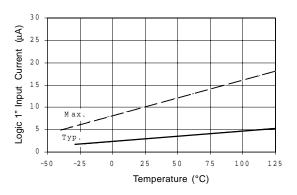


Figure 19A. Logic"1" Input Current vs Temperature

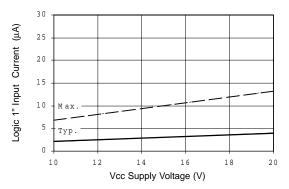


Figure 19B. Logic"1" Input Current vs Voltage

## International TOR Rectifier

## IR2104(S)&(PbF)

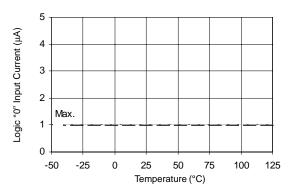
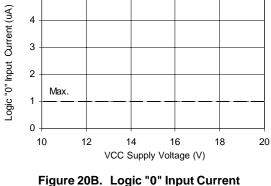


Figure 20A. Logic "0" Input Current vs Temperature



5

Figure 20B. Logic "0" Input Current vs Voltage

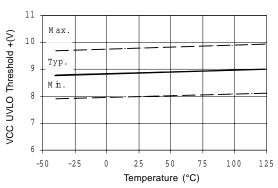


Figure 21A. Vcc Undervoltage Threshold(+) vs Temperature

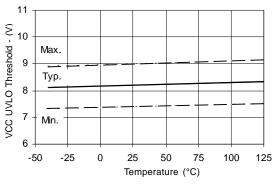


Figure 21B. Vcc Undervoltage Threshold(-) vs Temperature

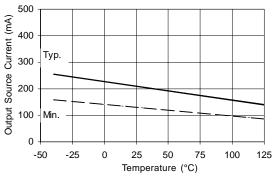


Figure 22A. Output Source Current vs Temperature

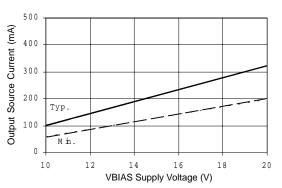


Figure 22B. Output Source Current vs Voltage

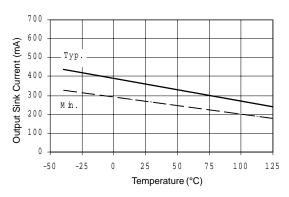


Figure 23A. Output Sink Current vs Temperature

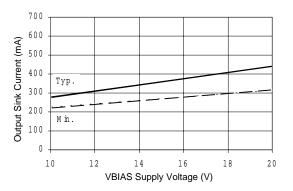
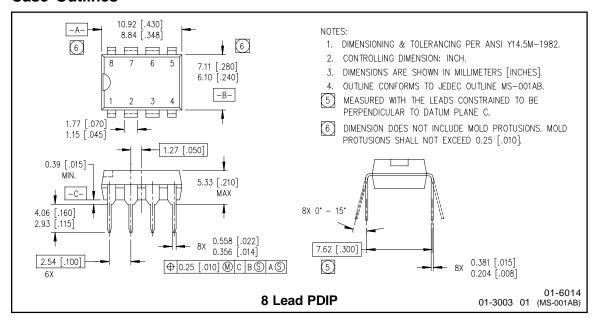
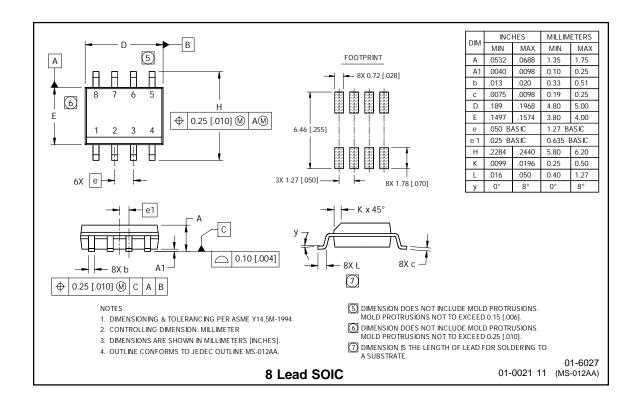


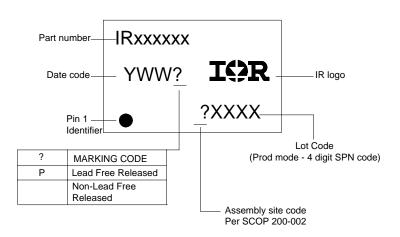
Figure 23B. Output Sink Current vs Voltage

#### **Case Outlines**





### LEADFREE PART MARKING INFORMATION



### **ORDER INFORMATION**

#### **Basic Part (Non-Lead Free)**

8-Lead PDIP IR2104 order IR2104 8-Lead SOIC IR2104S order IR2104S

#### Leadfree Part

8-Lead PDIP IR2104 order IR2104PbF 8-Lead SOIC IR2104S order IR2104SPbF

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IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245 Tel: (310) 252-7105

This product has been qualified per industrial level

Data and specifications subject to change without notice. 4/2/2004